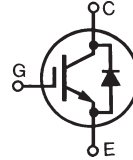


High Voltage, High Gain BiMOSFET™

IXBK64N250 IXBX64N250

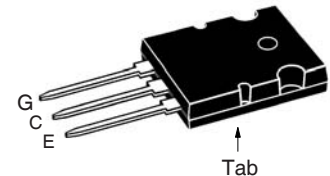
$V_{CES} = 2500V$
 $I_{C110} = 64A$
 $V_{CE(sat)} \leq 3.0V$

Monolithic Bipolar MOS Transistor

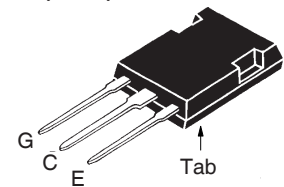


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	2500	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	2500	V
V_{GES}	Continuous	± 25	V
V_{GEM}	Transient	± 35	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	156	A
I_{LRMS}	Lead Current Limit, RMS	120	A
I_{C100}	$T_C = 110^\circ C$	64	A
I_{CM}	$T_C = 25^\circ C$, 1ms	600	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$	$I_{CM} = 160$	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq 0.8 \cdot V_{CES}$	
T_{SC} (SCSOA)	$V_{GE} = 15V$, $T_J = 125^\circ C$, $R_G = 5\Omega$, $V_{CE} = 1250V$, Non-Repetitive	10	μs
P_C	$T_C = 25^\circ C$	735	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in.
F_c	Mounting Force (PLUS247)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXBK)



PLUS247™ (IXBX)



G = Gate C = Collector
 E = Emitter Tab = Collector

Features

- High Blocking Voltage
- Low Switching Losses
- High Current Handling Capability
- Anti-Parallel Diode

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterrupted Power Supplies (UPS)
- Capacitor Discharge Circuits
- Laser Generators

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 1mA$, $V_{GE} = 0V$	2500		V
$V_{GE(th)}$	$I_C = 4mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			50 μA 6 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 25V$			± 200 nA
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$		2.5 3.1	V V

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.
g_{fs}	$I_C = I_{C110}, V_{CE} = 10V, \text{Note 1}$	40	72	S
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1\text{MHz}$		8900	pF
C_{oes}			345	pF
C_{res}			118	pF
Q_g	$I_C = I_{C110}, V_{GE} = 15V, V_{CE} = 600V$		400	nC
Q_{ge}			46	nC
Q_{gc}			155	nC
$t_{d(on)}$	Resistive Switching Times, $T_J = 25^\circ\text{C}$ $I_C = 128A, V_{GE} = 15V, t_p = 1\mu s$ $V_{CE} = 1250V, R_G = 1\Omega$		49	ns
t_r			318	ns
$t_{d(off)}$			232	ns
t_f			170	ns
$t_{d(on)}$	Resistive Switching Times, $T_J = 125^\circ\text{C}$ $I_C = 128A, V_{GE} = 15V, t_p = 1\mu s$ $V_{CE} = 1250V, R_G = 1\Omega$		54	ns
t_r			578	ns
$t_{d(off)}$			222	ns
t_f			175	ns
R_{thJC}				0.17 $^\circ\text{C/W}$
R_{thCS}		0.15		$^\circ\text{C/W}$

Reverse Diode

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

		Min.	Typ.	Max.
V_F	$I_F = I_{C110}, V_{GE} = 0V, \text{Note 1}$			3.0 V
t_{rr}	$I_F = I_{C110}, V_{GE} = 0V, -di_F/dt = 650A/\mu s$ $V_R = 600V, V_{GE} = 0V$		160	ns
I_{RM}			480	A

Note 1: Pulse test, $t \leq 300\mu s$, duty cycle, $d \leq 2\%$.

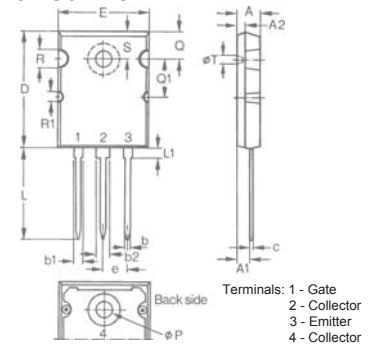
Additional provisions for lead-to-lead isolation are required at $V_{CE} > 1200V$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

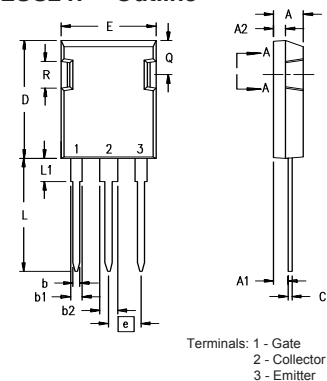
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4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A1	2.29	2.54	.090	.100
A2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b1	1.91	2.13	.075	.084
b2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

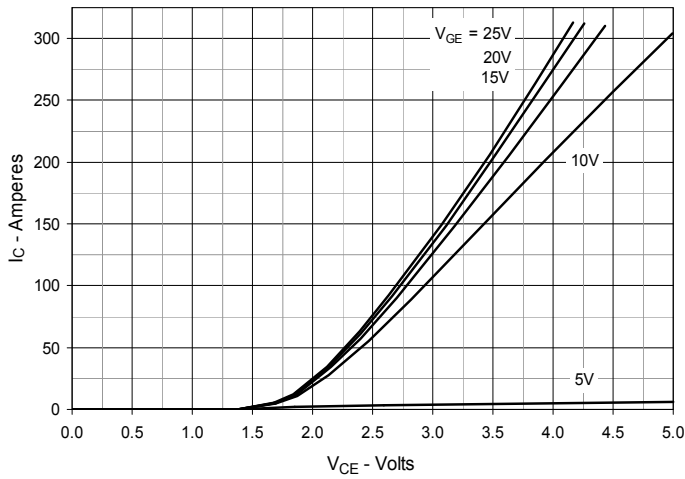
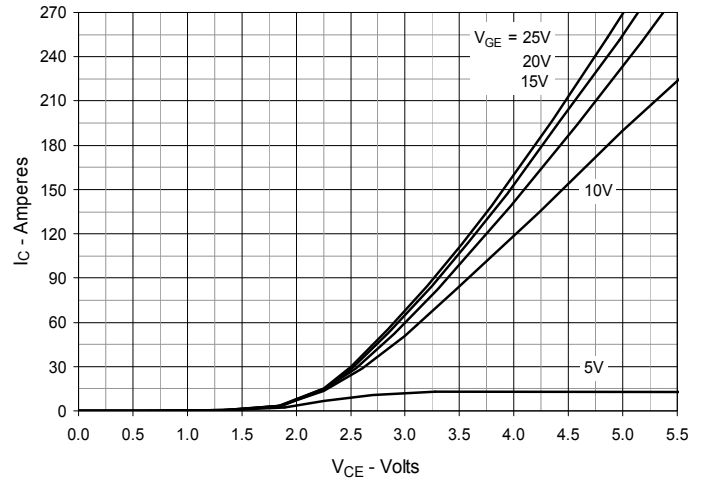
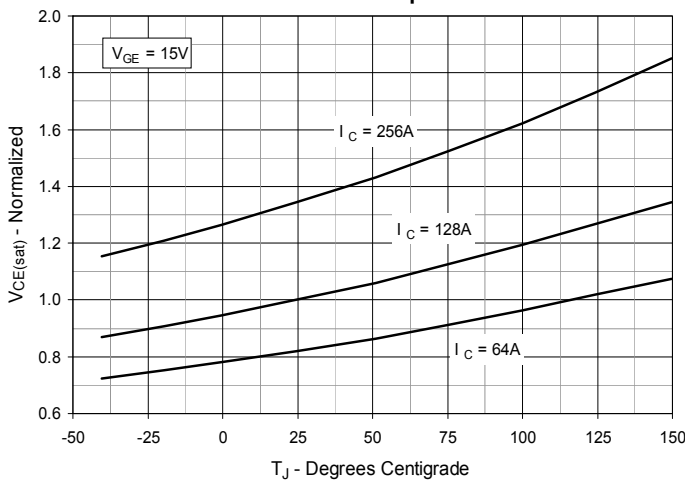
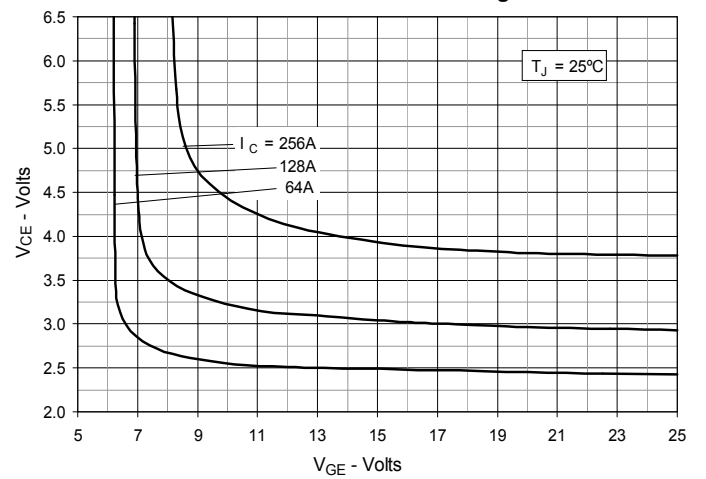
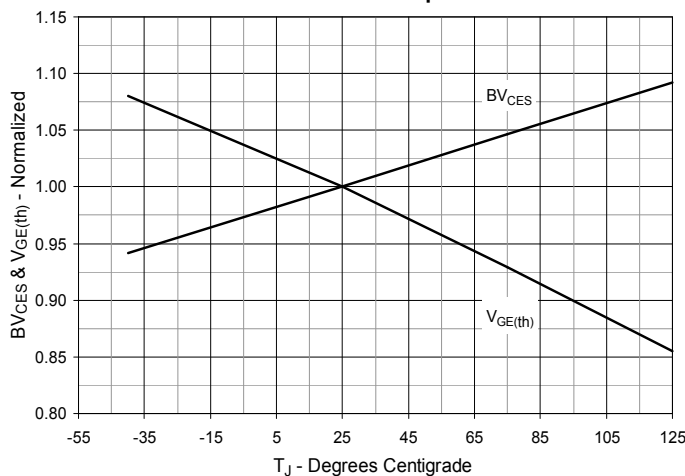
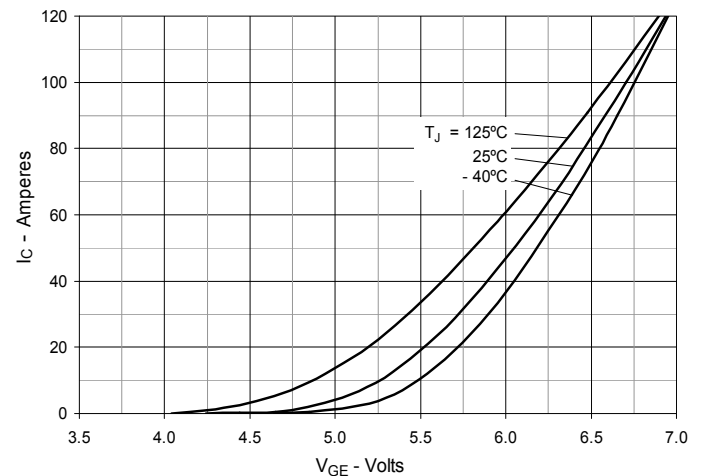
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 5. Breakdown & Threshold Voltages vs. Junction Temperature

Fig. 6. Input Admittance


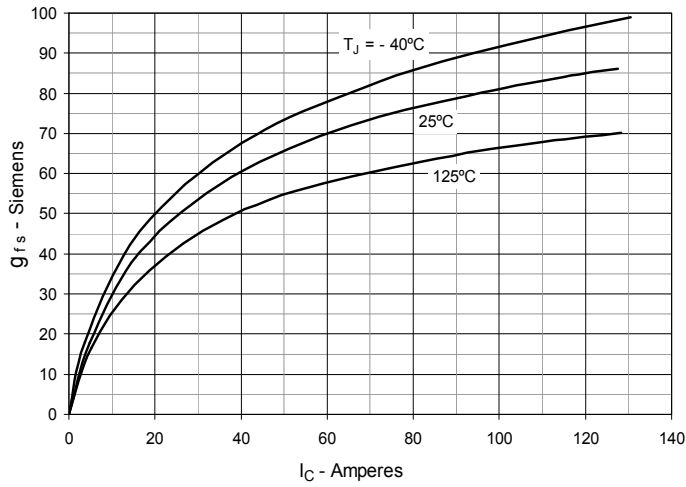
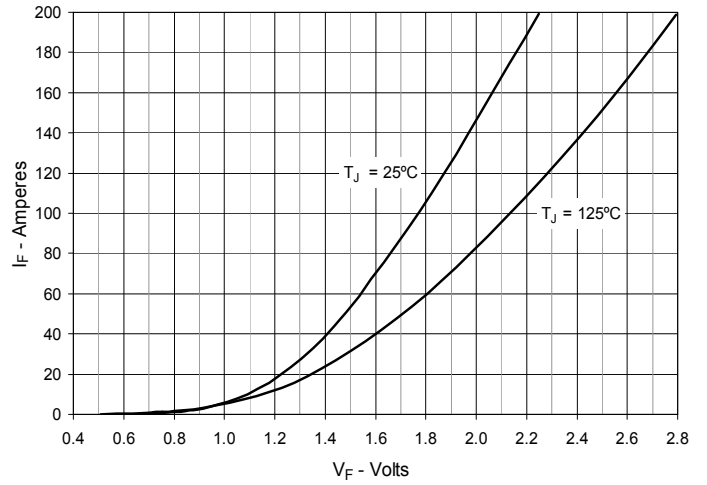
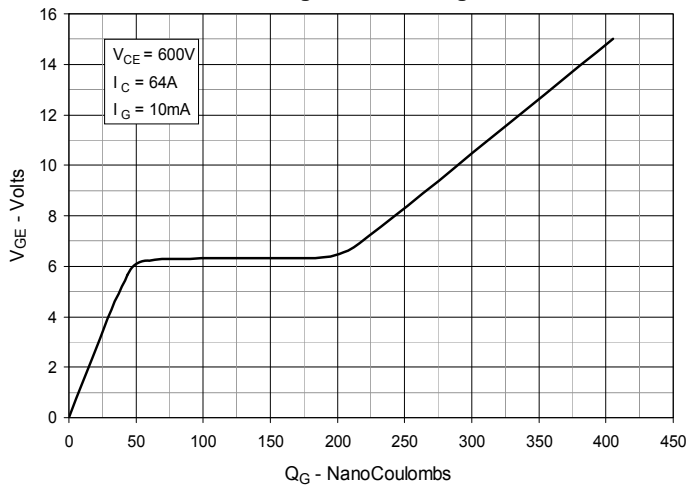
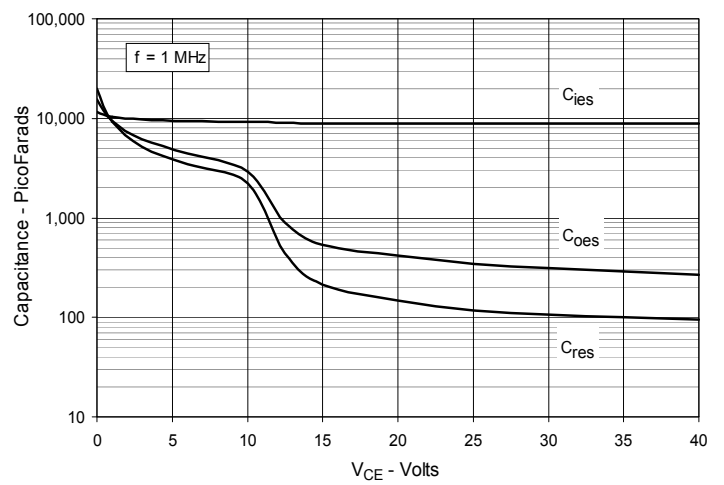
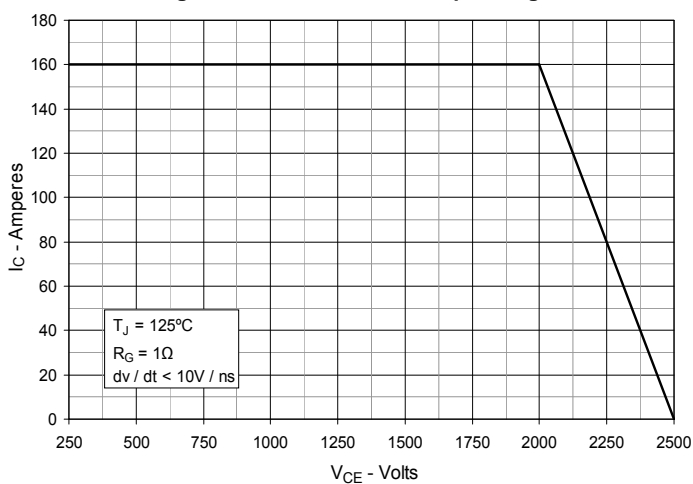
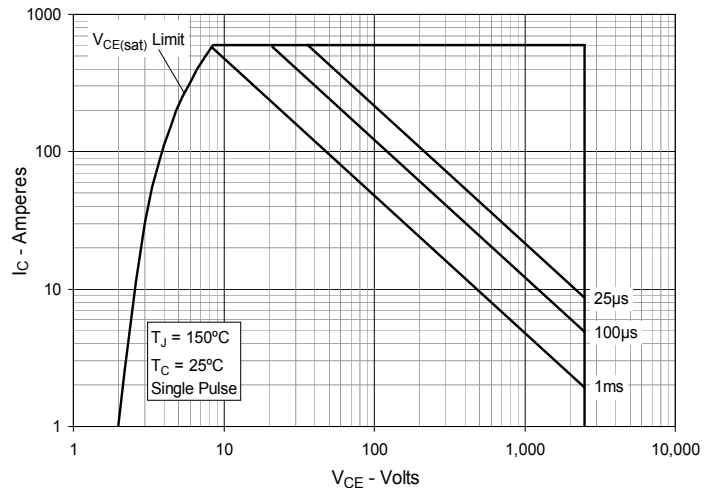
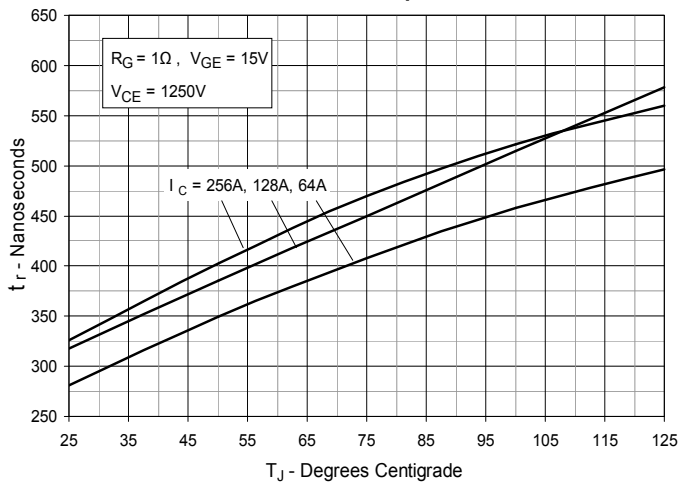
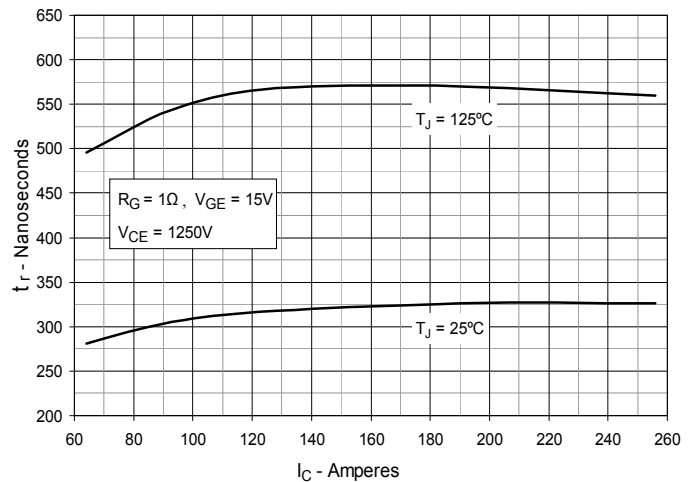
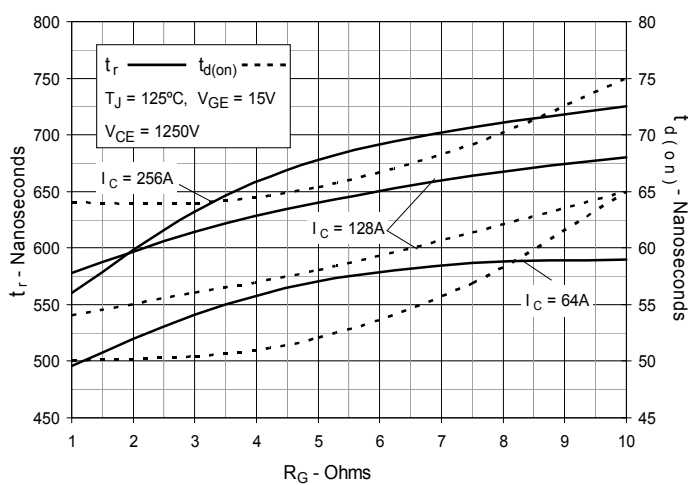
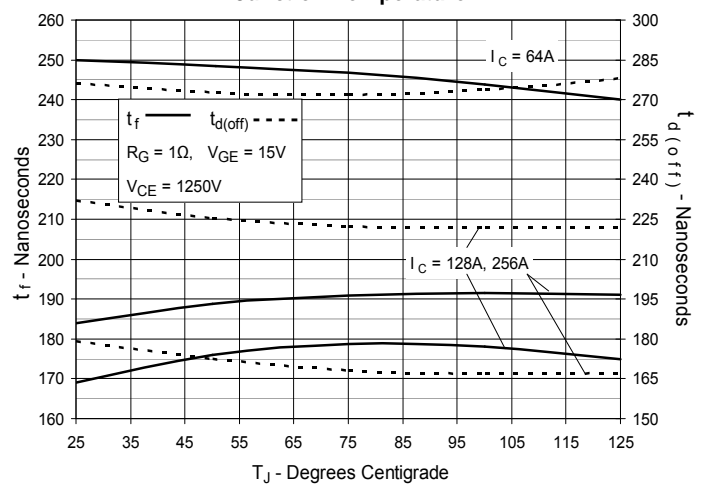
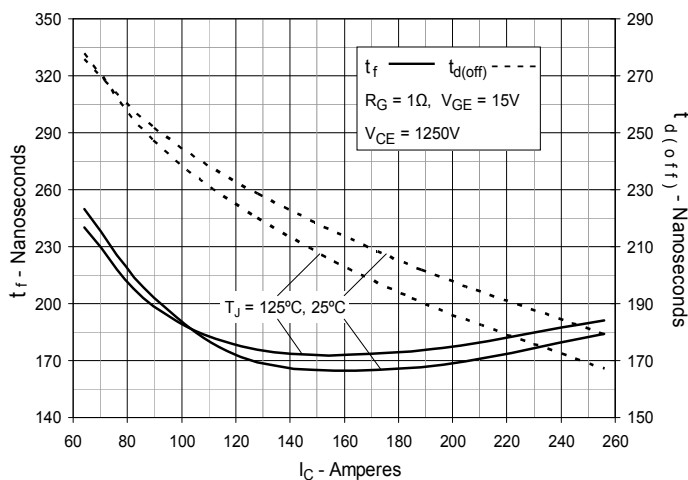
Fig. 7. Transconductance

Fig. 8. Forward Voltage Drop of Intrinsic Diode

Fig. 9. Gate Charge

Fig. 10. Capacitance

Fig. 11. Reverse-Bias Safe Operating Area

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance
